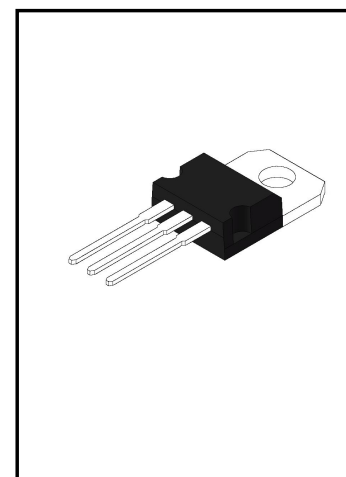
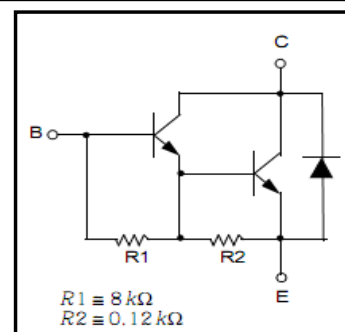


PNP Epitaxial Darlington Transistor**Medium Power Linear Switching Applications**

- Complementary to TIP120/121/122

Absolute Maximum Rating (Ta=25°C)

Parameter		Symbol	Value			Unit
			TIP125	TIP126	TIP127	
Collector-Base Voltage		V _{CBO}	-60	-80	-100	V
Collector-Emitter Voltage		V _{CEO}	-60	-80	-100	V
Emitter-Base Voltage		V _{EBO}	-5			V
Collector Current(DC)		I _C	-5			A
Collector Dissipation	T _a =25 °C	P _C	2			W
	T _C =25 °C		65			
Junction Temperature		T _j	150			°C
Storage Temperature		T _{stg}	-65~150			°C

**Electrical Characteristics (Ta=25°C)**

Parameter		Symbol	Conditions	Value			Unit
				Min	Typ	Max	
Collector-Emitter Sustaining Voltage	TIP125 TIP126 TIP127	V _{CEO(sus)}	I _C = -100mA, I _B = 0	-60 -80 -120			V
Collector cut-off current	TIP125 TIP126 TIP127	I _{CBO}	V _{CB} = -60V, I _E = 0 V _{CB} = -80V, I _E = 0 V _{CB} = -100V, I _E = 0			-1	mA
Collector cut-off current	TIP125 TIP126 TIP127	I _{CEO}	V _{CE} = -30V, I _E = 0 V _{CE} = -40V, I _E = 0 V _{CE} = -50V, I _E = 0			-2	mA
Emitter cut-off current			V _{EB} = -5V, I _C = 0			-2	mA
* DC current gain		h _{FE}	V _{CE} = -3V, I _C = -0.5A V _{CE} = -3V, I _C = -3A	1000 1000			
*Collector-emitter saturation voltage		V _{CE(sat)}	I _C = -3A, I _B = -12mA I _C = -5A, I _B = -20mA			-2 -4	V
* Base-Emitter ON Voltage		V _{BE (on)}	V _{CE} = -3V, I _C = -3A			-2.5	V
Output Capacitance		C _{ob}	V _{CB} = -10V, I _E = 0, f = 0.1MHz			200	pF

* Pulse Test : PW ≤ 300μs, Duty cycle ≤ 2%